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## Correction: A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranlydene thin films as observed in field-effect transistors and by conductive atomic force microscopy

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Correction for 'A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranlydene thin films as observed in field-effect transistors and by conductive atomic force microscopy' by Marc Courté *et al.*, *RSC Adv.*, 2017, 7, 3336–3342.

The authors regret that the name of the sixth author was presented incorrectly in the original article. Subodh G. Mhaisalkar's name has been corrected herein.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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